Standard Products

UT54ACS245S

Schmitt Octal Bus Transceiver with Three-State Outputs

Datasheet November 2010 www.aeroflex.com/logic



FEATURES ☐ Three-state outputs drive bus line directly □ 1.2µ CMOS - Latchup immune

- ☐ High speed
- ☐ Low power consumption ☐ Single 5 volt supply
- ☐ Available QML Q or V processes
- ☐ Flexible package
 - 20-pin DIP
 - 20-lead flatpack
- ☐ UT54ACS245S SMD 5962-96572

DESCRIPTION

The UT54ACS245S is a non-inverting octal bus transceiver with Schmitt Trigger input levels. The circuit is designed for asynchronous two-way communication between data buses. The control function implementation minimizes external timing requirements.

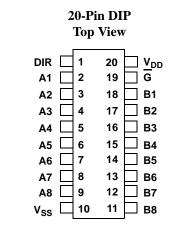
The device allows data transmission from the A bus to the B bus or from the B bus to the A bus depending upon the logic level at the direction control (DIR) input. The enable input (\overline{G}) disables the device so that the buses are effectively isolated.

The device is characterized over full military temperature range of -55°C to +125°C.

FUNCTION TABLE

EN <u>AB</u> LE G	DIRECTION CONTROL DIR	OPERATION	
L	L	B Data To A Bus	
L	Н	A Data To B Bus	
Н	Х	Isolation	

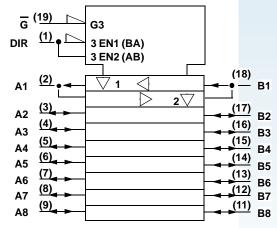
PINOUTS



20-Lead Flatpack Top View

DIR [1	20	V _{DD}
A 1 [2	19	G
A2 [3	18	B1
A3 [4	17	B2
A4 [5	16	В3
A5 [6	15	B4
A6 🛚	7	14	B5
A7 🛚	8	13	B6
A8 [9	12	B7
V _{SS}	10	11	B8

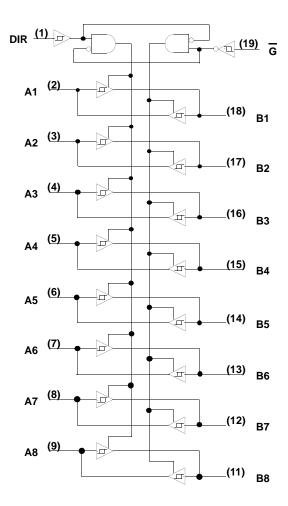
LOGIC SYMBOL



Note:

1. Logic symbol in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

LOGIC DIAGRAM



OPERATIONAL ENVIRONMENT¹

PARAMETER	LIMIT	UNITS
Total Dose	1.0E6	rads(Si)
SEU Threshold ²	80	MeV-cm ² /mg
SEL Threshold ³	120	MeV-cm ² /mg
Neutron Fluence	1.0E14	n/cm ²

Notes:

- $1. \ Logic \ will \ not \ latchup \ during \ radiation \ exposure \ within \ the \ limits \ defined \ in \ the \ table.$
- 2. Device storage elements are immune to SEU affects.

ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	LIMIT	UNITS
V _{DD}	Supply voltage	-0.3 to 7.0	V
V _{I/O}	Voltage any pin	3 to V _{DD} +.3	V
T _{STG}	Storage Temperature range	-65 to +150	°C
T _J	Maximum junction temperature	+175	°C
T _{LS}	Lead temperature (soldering 5 seconds)	+300	°C
$\Theta_{ m JC}$	Thermal resistance junction to case	20	°C/W
I _I	DC input current	±10	mA
P_{D}	Maximum power dissipation	1	W

Note:

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIMIT	UNITS
V _{DD}	Supply voltage	4.5 to 5.5	V
V_{IN}	Input voltage any pin	0 to V _{DD}	V
T _C	Temperature range	-55 to + 125	°C

^{1.} Stresses outside the listed absolute maximum ratings may cause permanent damage to the device. This is a stress rating only, functional operation of the device at these or any other conditions beyond limits indicated in the operational sections is not recommended. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

DC ELECTRICAL CHARACTERISTICS 7

 $(V_{DD} = 5.0V \pm 10\%; V_{SS} = 0V^6, -55^{\circ}C < T_C < +125^{\circ}C);$ Unless otherwise noted, Tc is per the temperature range ordered.

SYMBOL	PARAMETER	CONDITION	MIN	MAX	UNIT
V_{T} +	Schmitt Trigger, positive going threshold ¹ ACS			.7V _{DD}	V
V _T	Schmitt Trigger, negative going threshold ¹ ACS		.3V _{DD}		V
V _H	Schmitt Trigger, typical range of hysteresis ACS		0.6	1.5	v
I _{IN}	Input leakage current ACS	$V_{IN} = V_{DD}$ or V_{SS}	-1	1	μА
V _{OL}	Low-level output voltage ³ ACS	$I_{OL} = 100 \mu A$		0.25	V
V _{OH}	High-level output voltage ³ ACS	$I_{OH} = -100 \mu A$	V _{DD} - 0.25		V
I _{OL}	Output current (Sink) ¹⁰	$V_{IN}=V_{DD}$ or V_{SS} $V_{OL}=0.4V$	12		mA
I _{OH}	Output current (Source) ¹⁰	$V_{IN}=V_{DD}$ or V_{SS} $V_{OH}=V_{DD}$ - 0.4	-12		mA
I_{OZ}	Three-state output leakage current	$V_O = V_{DD}$ and V_{SS}	-30	30	μΑ
I _{OS}	Short-circuit output current ^{2, 4} ACS	$V_{O} = V_{DD}$ and V_{SS}	-300	300	mA
P _{total}	Power dissipation ^{2, 8, 9}	$C_L = 50pF$		2.0	mW/ MHz
I_{DDQ}	Quiescent Supply Current	$V_{DD} = 5.5V$		10	μΑ
C _{IN}	Input capacitance ⁵	f = 1MHz @ 0V		15	pF
C _{OUT}	Output capacitance ⁵	f = 1MHz @ 0V		15	pF

Notes:

- 1. Functional tests are conducted in accordance with MIL-STD-883 with the following input test conditions: $V_{IH} = V_{IH}(min) + 20\%$, -0%; $V_{IL} = V_{IL}(max) + 0\%$, -0%; 50%, as specified herein, for TTL, CMOS, or Schmitt compatible inputs. Devices may be tested using any input voltage within the above specified range, but are guaranteed to V_{IH}(min) and V_{IL}(max).
- 2. Supplied as a design limit, but not guaranteed or tested.
- 3. Per MIL-PRF-38535, for current density ≤ 5.0E5 amps/cm², the maximum product of load capacitance (per output buffer) times frequency should not exceed 3,765 pF/MHz.

 4. Not more than one output may be shorted at a time for maximum duration of one second.
- 5. Capacitance measured for initial qualification and when design changes may affect the value. Capacitance is measured between the designated terminal and V_{SS} at frequency of 1MHz and a signal amplitude of 50mV rms maximum.
- 6. Maximum allowable relative shift equals 50mV.
- 7. All specifications valid for radiation dose \leq 1E6 rads(Si).
- 8. Power does not include power contribution of any TTL output sink current.
- 9. Power dissipation specified per switching output.
- 10. Guaranteed based on characterization data, but not tested.

AC ELECTRICAL CHARACTERISTICS 2

 $(V_{DD} = 5.0V \pm 10\%; \ V_{SS} = \ 0V^6, \ -55^\circ C < T_C < +125^\circ C); \ Unless \ otherwise \ noted, \ Tc \ is \ per \ the \ temperature \ range \ ordered.$

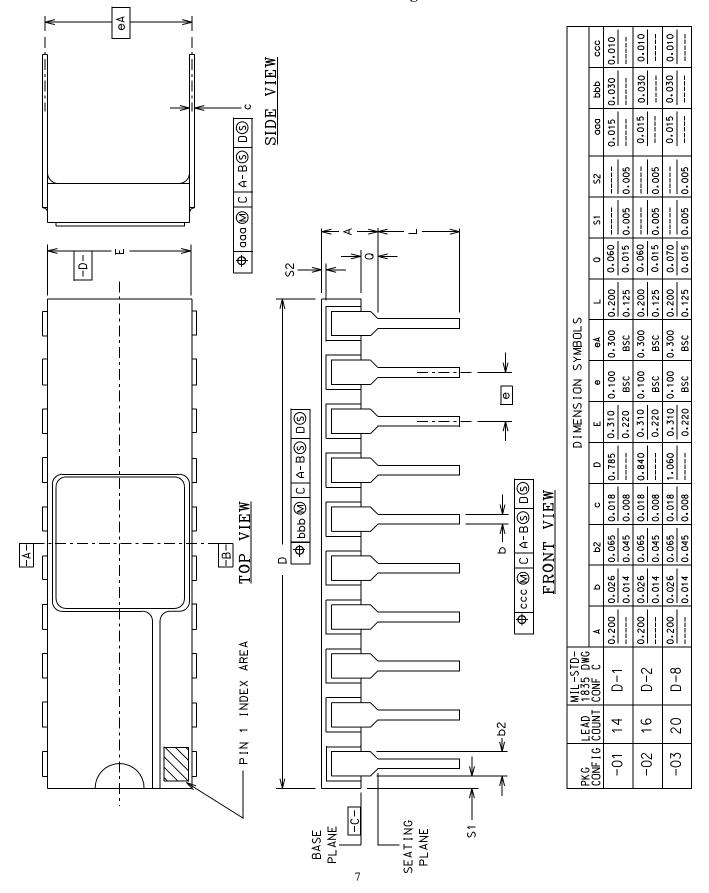
SYMBOL	PARAMETER	MINIMUM	MAXIMUM	UNIT
t _{PLH}	Data to bus	2	15	ns
t _{PHL}	Data to bus	2	15	ns
t _{PZL}	G low to bus active	2	12	ns
t _{PZH}	G low to bus active	2	12	ns
t _{PLZ}	G high to bus three-state	2	15	ns
t _{PHZ}	G high to bus three-state	2	15	ns

Notes:

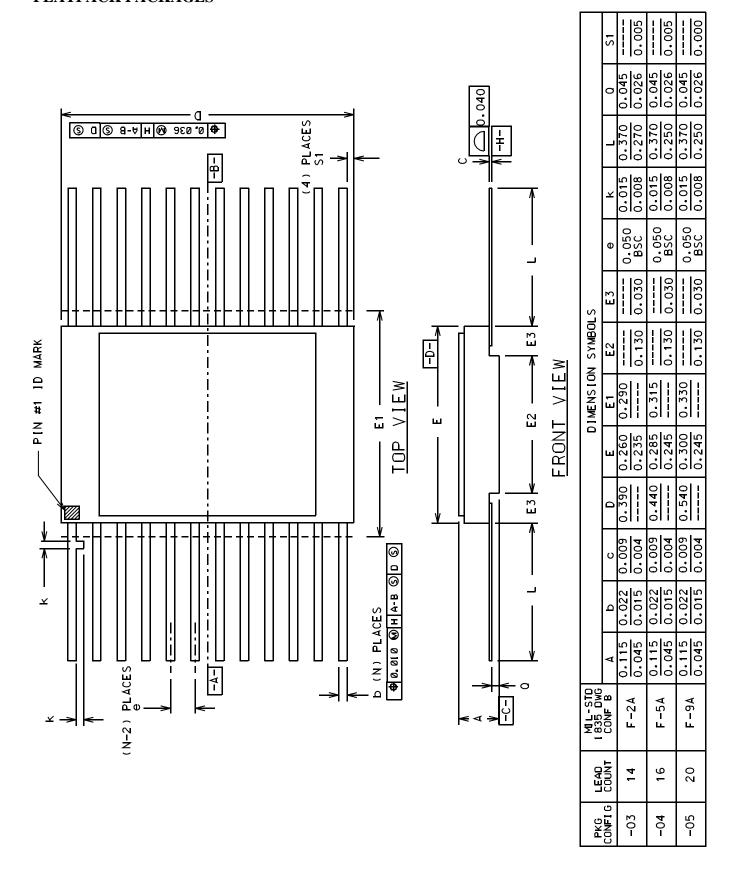
Maximum allowable relative shift equals 50mV.
 All specifications valid for radiation dose ≤ 1E6 rads(Si)

PACKAGING

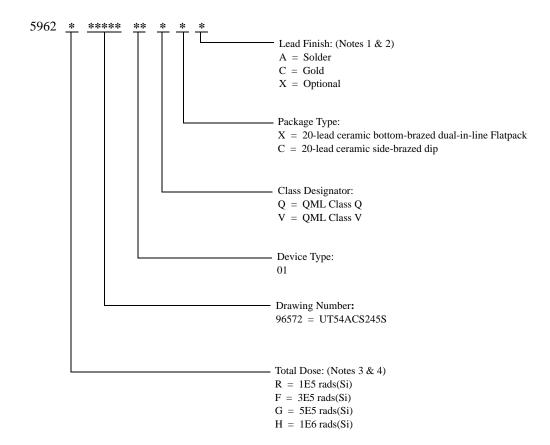
Side-Brazed Packages



FLATPACK PACKAGES



UT54ACS245S: SMD



Notes:

- 1. Lead finish (A,C, or X) must be specified.
- 2. If an "X" is specified when ordering, part marking will match the lead finish and will be either "A" (solder) or "C" (gold).
- $3. \ Total \ dose \ radiation \ must \ be \ specified \ when \ ordering. \ QML \ Q \ and \ QML \ V \ not \ available \ without \ radiation \ hardening. For \ prototype \ inquiries, \ contact \ factory.$
- 4. Device type 02 is only offered with a TID tolerance guarantee of 3E5 rads(Si) or 1E6 rads(Si) and is tested in accordance with MIL-STD-883 Test Method 1019 Condition A and section 3.11.2. Device type 03 is only offered with a TID tolerance guarantee of 1E5 rads(Si), 3E5 rads(Si), and 5E5 rads(Si), and is tested in accordance with MIL-STD-883 Test Method 1019 Condition A.

Aeroflex Colorado Springs - Datasheet Definition

Advanced Datasheet - Product In Development

Preliminary Datasheet - Shipping Prototype

Datasheet - Shipping QML & Reduced Hi-Rel

COLORADO

Toll Free: 800-645-8862 Fax: 719-594-8468

SE AND MID-ATLANTIC

www.aeroflex.com

Tel: 321-951-4164 Fax: 321-951-4254 INTERNATIONAL

Tel: 805-778-9229 Fax: 805-778-1980

WEST COAST

Tel: 949-362-2260 Fax: 949-362-2266 NORTHEAST

Tel: 603-888-3975 Fax: 603-888-4585

CENTRAL

Tel: 719-594-8017 Fax: 719-594-8468

info-ams@aeroflex.com

Aeroflex UTMC Microelectronic Systems Inc. (Aeroflex) reserves the right to make changes to any products and

services herein at any time without notice. Consult Aeroflex or an authorized sales representative to verify that the information in this data sheet is current before using this product. Aeroflex does not assume any responsibility or liability arising out of the application or use of any product or service described herein, except as expressly agreed to in writing by Aeroflex; nor does the purchase, lease, or use of a product or service from Aeroflex convey a license under any patent rights, copyrights, trademark rights, or any other of the intellectual rights of Aeroflex or of third parties.









Our passion for performance is defined by three attributes represented by these three icons: solution-minded, performance-driven and customer-focused